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10/685.597

Filing Date

October 16, 2003

**First Named Inventor**

Kong et al.

### Group Art Unit

2812

Examiner Name \_\_\_\_\_

[illegible]

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sub>0</sub>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
PD	10	WO	99/18617		Cree Research, Inc.	04-15-1999		
↑	11	Japan	9-174494		Nichia Chemical Industries, Inc.	06-30-1997		x
	12	Japan	9-201477		" "	07-28-1997		x
	13	Japan	9-277448		" "	10-09-1997		x
	14	Japan	9-290098		" "	10-22-1997		x
	15	Japan	9-324997		" "	11-26-1997		x
	16	Japan	11-191657		" "	07-13-1999		
↓	17	Japan	07-273367		Mitsubishi Cable Industries, Ltd.	10-20-1995		
PD	18	Japan	9-093315		Nichia Chemical Industries, Inc.	04-11-1997		x

PHUC T. DANG

3/12/2005

Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449A/PTO				Complete If Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				Application Number	10/685,597
				Filing Date	October 16, 2003
				First Named Inventor	Kong et al.
				Group Art Unit	2812
				Examiner Name	
Sheet	2	of	4	Attorney Docket Number	5000.129D

[illegible]

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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>3</sup> (if known)				
PD	19	JP	10312971		NEC CORP.	11-24-1998		
↑	20	WO	99/23693	A	Sumitomo Electric Industries Ltd.	05-14-1999		
	21	EP	1041610	A1	Kensaku Motoki	04-2000		
	22	CA	2,258,080	A1	Nichia Chemical Industries, Ltd.	04-09-1998		
	23	WO	98/47170		" "	10-22-1998		
	24	WO	00/31783		North Carolina State University	06-02-2000		
	25	WO	00/33365		" "	06-08-2000		
	26	WO	99/65068		" "	12-16-1999		
↓	27	EP	0 942 459	A1	Nichia Chemical Industries	09-15-1999		
	28	EP	1 005 067	A2	Sony Corp. Tokyo	05-31-2000		
PD	29	CN	1258094		Sony Corp	06-28-2000		

Examiner Signature	PHUOT. DANG	Date Considered	3/12/2005
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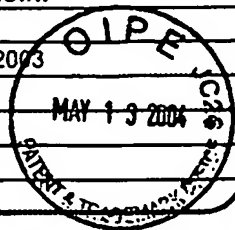


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Substitute for form 1449A/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/685,597
		Filing Date	October 16, 2003
		First Named Inventor	Kong et al.
		Group Art Unit	2812
		Examiner Name	
Sheet 3 of 4	Attorney Docket Number	5000.129D	



OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PD	30	DAVIS, ET AL., "Pendeo-epitaxial Growth and Characterization of GaN and Related Materials on 6H-SiC(0001) and Si(111) Substrates", Department of Materials Science and Engineering, North Carolina State University, F99W2.1	
	31	GEHRKE ET AL., "Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructures on Silicon Carbide Substrate", MRS Internet Journal Nitride Semiconductor Research 4S1, G3.2, 1999	
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PD	40	SHEALY ET AL., "Single Step Process for Epitaxial Lateral Overgrowth of GaN", The Heterogeneous Optoelectronics Technology Center: Quarterly Report, p. 9	

Examiner Signature	PHUC T. DANG	Date Considered	3/12/2005
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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

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of

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### Complete if Known

Application Number 10/685,597

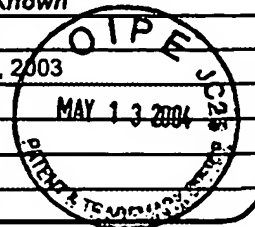
Filing Date October 16, 2003

First Named Inventor Kong et al.

Group Art Unit 2812

Examiner Name

Attorney Docket Number 5000.129D



### OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
PD	41	SMART, ET AL., "Single step process for epitaxial lateral overgrowth of GaN on SiC and sapphire substrates", Applied Physics Letters, Vol. 75, No. 24; December 1999, pp. 3820-3822	
	42	DUPUIS, R.D. et al., Selective-area and lateral epitaxial overgrowth of III-N materials by metalorganic chemical vapor deposition"; Journal of Crystal Growth, vol. 195, no. 1-4, December 1998 (1998-12), pages 340-345	
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	47	KIDOGUCHI, I. et al., Improvement of crystalline quality in GaN films by air-bridged lateral epitaxial growth, Japanese Journal of Applied Physics, Part 2 (Letters), vol. 39, no. 58, May 15, 2000, pages L453-L453	
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Signature

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